



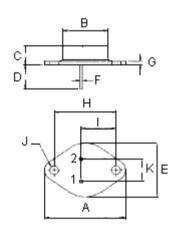
High voltage power transistor.

designed for use in high-voltage, high-speed, power switching in inductive circuit, motor control, solenoid and relay drivers.

Features:

- Collector-emitter sustaining voltage V_{CEO (sus)} = 4000V (Minimum).
 Low collector-emitter saturation voltage V_{CE (sat)} = 3.0V (Maximum) at I_C = 8.0A, I_B = 2.5A.

TO-3



Pin 1. Base 2. Emitter Collector (Case)

Dimensions	Minimum	Maximum
А	38.75	39.96
В	19.28	22.23
С	7.96	9.28
D	11.18	12.19
E	25.20	26.67
F	0.92	1.09
G	1.38	1.62
Н	29.90	30.40
I	16.64	17.30
J	3.88	4.36
К	10.67	11.18

Dimensions : Millimetres

NPN BUX80

10 Ampere Power **Transistors** 400 Volts 100 Watts



TO-3



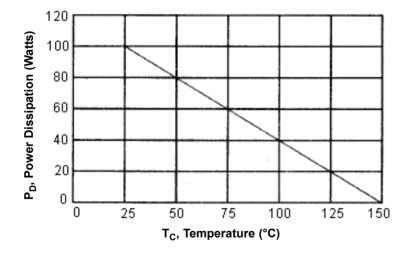
Maximum Ratings

Characteristic	Symbol	BUX80	Unit
Collector-Emitter Voltage	V _{CEO}	400	
Collector-Emitter Voltage (V _{BE} = 0)	V _{CES}	800	V
Emitter-Base Voltage	V _{EBO} 10		
Collector Current-Continuous -Peak	I _C	10 15	А
Base Current-Continuous	I _B	5.0	
Total Power Dissipation at T _C = 25°C Derate above 25°C	P _D	100 0.8	W W/°C
Operating and Storage Junction Temperature Range	T _J , T _{STG}	-65 to +200	°C

Thermal Characteristics

Characteristic	Symbol	Maximum	Unit
Thermal Resistance Junction to Case	Rθjc	1.25	°C/W

Power Derating





Electrical Characteristics (T_C = 25°C unless otherwise noted)

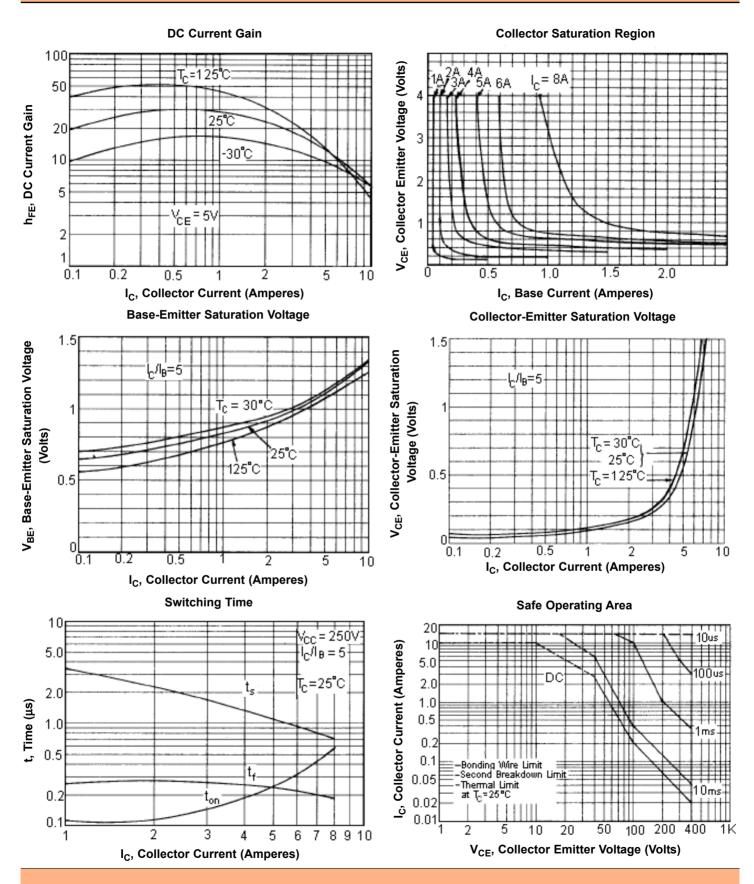
С	haracteristic	Symbol	Minimum	Maximum	Unit	
Off Characteristics						
Collector-Emitter Sustai (I _C = 100mA, I _B = 0, L =		V _{CEO (sus)}	400	-	V	
Collector Cut off Current ($V_{CE} = 800V$, $V_{BE} = 0$) ($V_{CE} = 800V$, $V_{BE} = 0$, $T_{C} = 125$ °C)		I _{CES}	-	1.0 3.0	mA	
Emitter Cut off Current (V _{EB} = 10V, I _C = 0)		I _{EBO}	-	10		
On Characteristics (1)						
DC Current Gain (I _C = 1.2A, V _{CE} = 5.0V)		h _{FE}	30 (typical)	-	-	
Collector-Emitter Satura ($I_C = 5.0A$, $I_B = 1.0mA$) ($I_C = 8.0A$, $I_B = 2.5mA$)	tion Voltage	V _{CE (sat)}	-	1.5 3.0	.,	
Base-Emitter Saturation Voltage ($I_C = 5.0A$, $I_B = 1.0mA$) ($I_C = 8.0A$, $I_B = 2.5mA$)		V _{BE (sat)}	-	1.4 1.8	V	
Switching Characteris	tics	<u>'</u>	•			
Turn On Time	V _{cc} = 250V, I _C = 5.0A	t _{on}	-	0.5		
Storage Time	I _{B1} = 1.0A, I _{B2} = -2.0A	t _s	-	3.5	μs	
Fall Time	-	t _f	-	0.5		

Page <3>



⁽¹⁾ Pulse Test : Pulse Width = 300µs, Duty Cycle ≤2.0%.





http://www.farnell.com http://www.newark.com http://www.cpc.co.uk



1165901



Part Number Table

Description	Part Number		
Transistor, NPN, TO-3	BUX80		

Disclaimer This data sheet and its contents (the "Information") belong to the Premier Farnell Group (the "Group") or are licensed to it. No licence is granted for the use of it other than for information purposes in connection with the products to which it relates. No licence of any intellectual property rights is granted. The Information is subject to change without notice and replaces all data sheets previously supplied. The Information supplied is believed to be accurate but the Group assumes no responsibility for its accuracy or completeness, any error in or omission from it or for any use made of it. Users of this data sheet should check for themselves the Information and the suitability of the products for their purpose and not make any assumptions based on information included or omitted. Liability for loss or damage resulting from any reliance on the Information or use of it (including liability resulting from negligence or where the Group was aware of the possibility of such loss or damage arising) is excluded. This will not operate to limit or restrict the Group's liability for death or personal injury resulting from its negligence. SPC Multicomp is the registered trademark of the Group. © Premier Farnell plc 2008.

http://www.farnell.com http://www.newark.com http://www.cpc.co.uk

